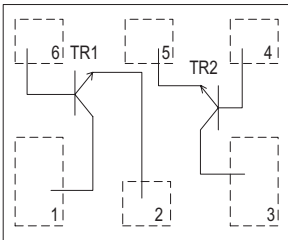
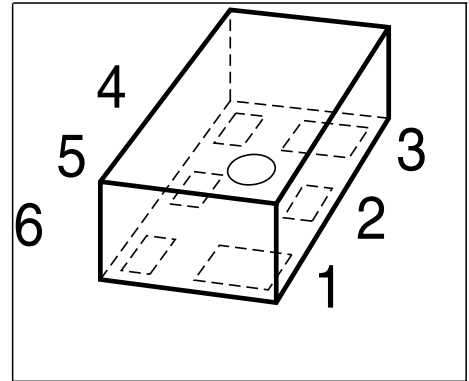


NPN Silicon RF Transistor

Preliminary data

- High current capability and low figure for wide dynamic range application
- Low voltage operation
- Ideal for low phase noise oscillators up to 3.5 GHz
- Low noise figure: 1.1 dB at 1.8 GHz
- Built in 2 transistors (TR1, TR2: die as BFR380L3)


ESD: Electrostatic discharge sensitive device, observe handling precaution!

Type	Marking	Pin Configuration						Package
BFS380L6	FC	1=C1	2=E1	3=C2	4=B2	5=E2	6=B1	TSLP-6-1

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	6	V
Collector-emitter voltage	V_{CES}	15	
Collector-base voltage	V_{CBO}	15	
Emitter-base voltage	V_{EBO}	2	
Collector current	I_C	80	mA
Base current	I_B	14	
Total power dissipation ¹⁾ $T_S \leq 96^\circ\text{C}$	P_{tot}	380	mW
Junction temperature	T_j	150	°C
Ambient temperature	T_A	-65 ... 150	
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾	R_{thJS}	≤ 140	K/W

¹⁾ T_S is measured on the collector lead at the soldering point to the pcb

²⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 1 \text{ mA}, I_B = 0$	$V_{(BR)CEO}$	6	9	-	V
Collector-emitter cutoff current $V_{CE} = 15 \text{ V}, V_{BE} = 0$	I_{CES}	-	-	10	μA
Collector-base cutoff current $V_{CB} = 5 \text{ V}, I_E = 0$	I_{CBO}	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 1 \text{ V}, I_C = 0$	I_{EBO}	-	-	1	μA
DC current gain- $I_C = 40 \text{ mA}, V_{CE} = 3 \text{ V}$	h_{FE}	60	130	200	-

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Transition frequency $I_C = 40\text{ mA}$, $V_{CE} = 3\text{ V}$, $f = 1\text{ GHz}$	f_T	-	14	-	GHz
Collector-base capacitance $V_{CB} = 5\text{ V}$, $f = 1\text{ MHz}$, emitter grounded	C_{cb}	-	0.5	-	pF
Collector emitter capacitance $V_{CE} = 5\text{ V}$, $f = 1\text{ MHz}$, base grounded	C_{ce}	-	0.2	-	
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$, collector grounded	C_{eb}	-	1.1	-	
Noise figure $I_C = 8\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_{Sopt}$, $f = 1.8\text{ GHz}$ $I_C = 8\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_{Sopt}$, $f = 3\text{ GHz}$	F_{min}	-	1.3 1.9	-	dB
Power gain, maximum available ¹⁾ $I_C = 40\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$, $f = 1.8\text{ GHz}$ $I_C = 40\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$, $f = 3\text{ GHz}$	G_{ma}	-	12 8	-	
Transducer gain $I_C = 40\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_L = 50\Omega$, $f = 1.8\text{ GHz}$ $I_C = 40\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_L = 50\Omega$, $f = 3\text{ GHz}$	$ S_{21e} ^2$	-	10 6.5	-	dB
Third order intercept point at output ²⁾ $V_{CE} = 3\text{ V}$, $I_C = 40\text{ mA}$, $f = 1.8\text{ GHz}$, $Z_S = Z_L = 50\Omega$	IP_3	-	27	-	dBm
1dB Compression point at output $I_C = 40\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_L = 50\Omega$, $f = 1.8\text{ GHz}$	P_{-1dB}	-	11.5	-	

$$^1G_{ma} = |S_{21e}| / |S_{12e}| (k - (k^2 - 1)^{1/2})$$

²⁾IP3 value depends on termination of all intermodulation frequency components.
Termination used for this measurement is 50Ω from 0.1 MHz to 6 GHz

单击下面可查看定价，库存，交付和生命周期等信息

[>>Infineon\(英飞凌\)](#)